

BCW66GLT1G, SBCW66GLT1G

General Purpose Transistor

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	45	Vdc
Collector–Base Voltage	V_{CBO}	75	Vdc
Emitter–Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	800	mAdc
Collector Current – Pulsed	I_C	1200	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

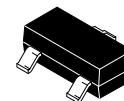
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1), $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

1. FR–5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

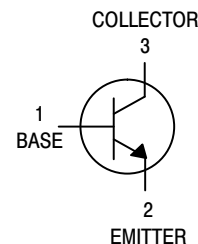


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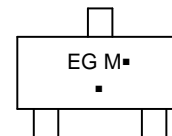
www.onsemi.com



SOT-23
(TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



EG = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(*Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BCW66GLT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SBCW66GLT1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
BCW66GLT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BCW66GLT1G, SBCW66GLT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	45	–	–	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 10\text{ }\mu\text{Adc}$, $V_{EB} = 0$)	$V_{(BR)CES}$	75	–	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	5.0	–	–	Vdc
Collector Cutoff Current ($V_{CE} = 45\text{ Vdc}$, $I_E = 0$) ($V_{CE} = 45\text{ Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)	I_{CES}	–	–	20	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 4.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	–	20	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 100\text{ }\mu\text{Adc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 500\text{ mAdc}$, $V_{CE} = 2.0\text{ Vdc}$)	h_{FE}	50 110 160 60	– – – –	– – 400 –	–
Collector–Emitter Saturation Voltage ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$) ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{CE(sat)}$	– –	– –	0.7 0.3	Vdc
Base–Emitter Saturation Voltage ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)	$V_{BE(sat)}$	–	–	2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 20\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	–	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	–	12	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	–	80	pF
Noise Figure ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 0.2\text{ mAdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	–	–	10	dB

SWITCHING CHARACTERISTICS

Turn–On Time ($I_{B1} = I_{B2} = 15\text{ mAdc}$)	t_{on}	–	–	100	ns
Turn–Off Time ($I_C = 150\text{ mAdc}$, $R_L = 150\text{ }\Omega$)	t_{off}	–	–	400	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

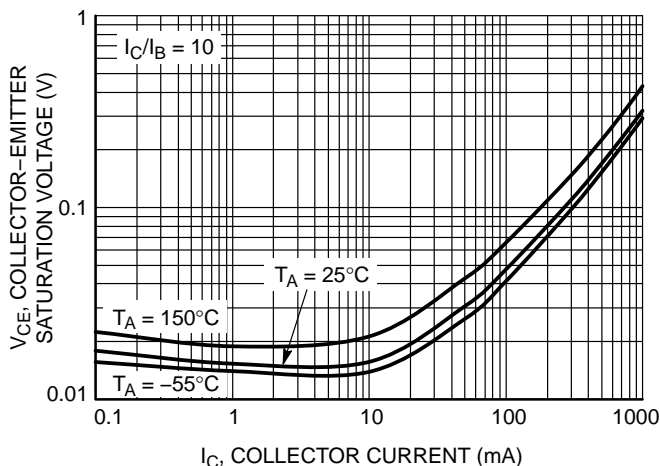


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

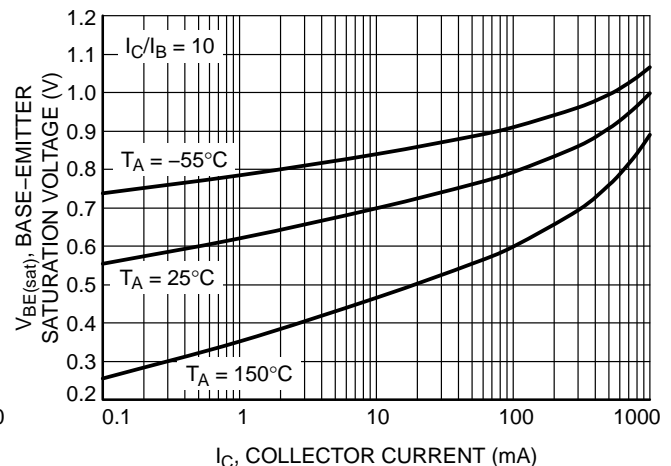


Figure 2. Base Emitter Saturation Voltage vs. Collector Current

BCW66GLT1G, SBCW66GLT1G

TYPICAL CHARACTERISTICS

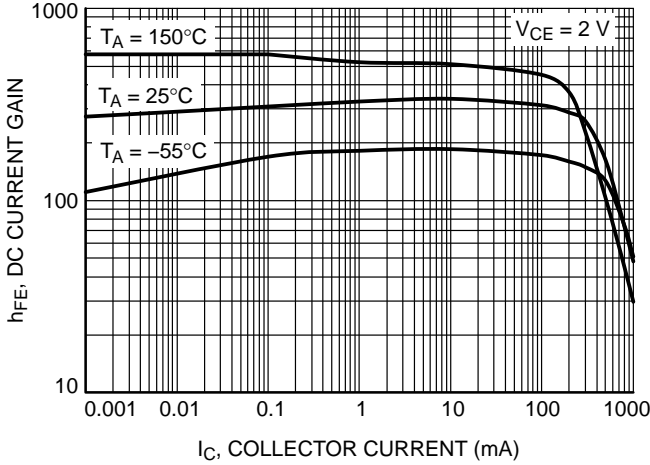


Figure 3. DC Current Gain vs. Collector Current

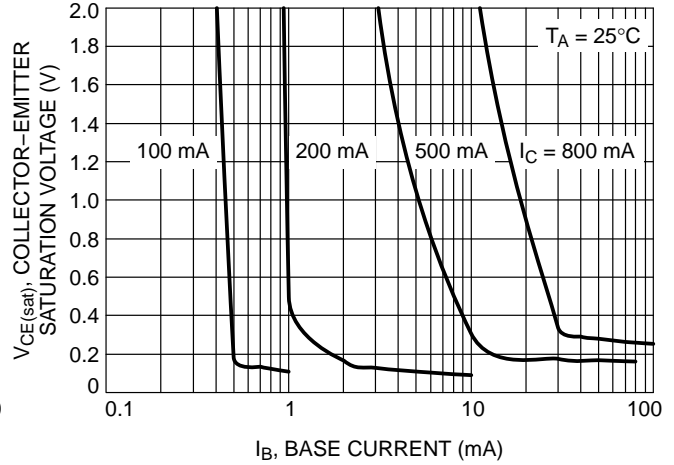


Figure 4. Saturation Region

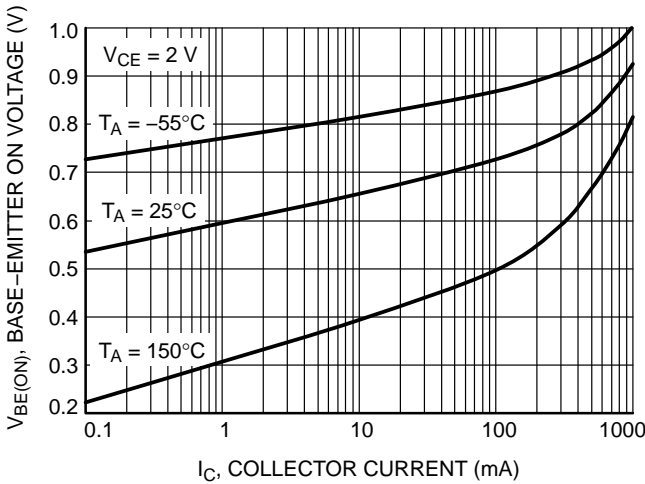


Figure 5. Base-Emitter Turn-On Voltage vs. Collector Current

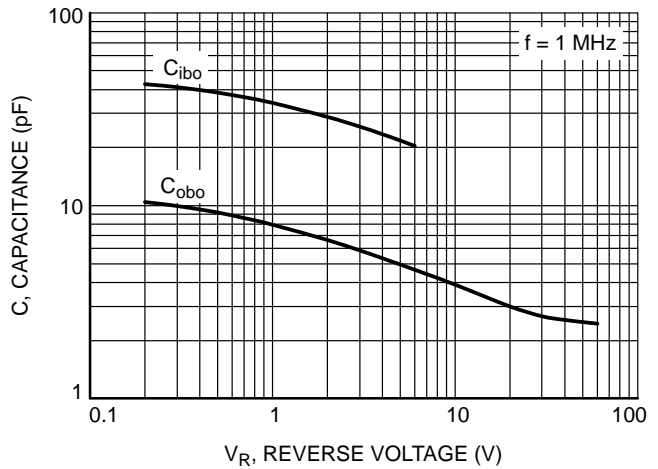


Figure 6. Capacitance

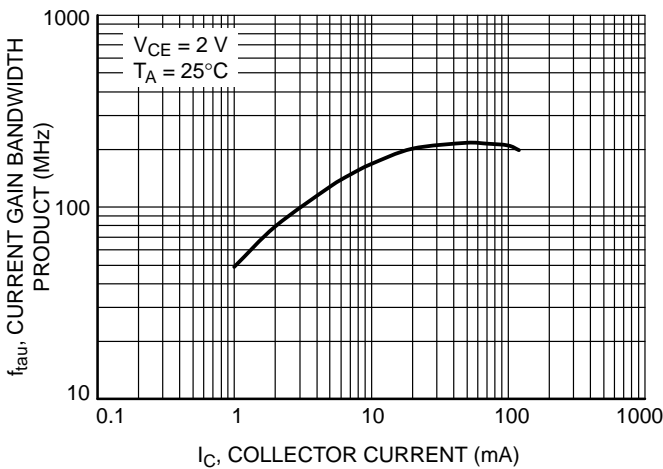


Figure 7. Current Gain Bandwidth Product vs. Collector Current

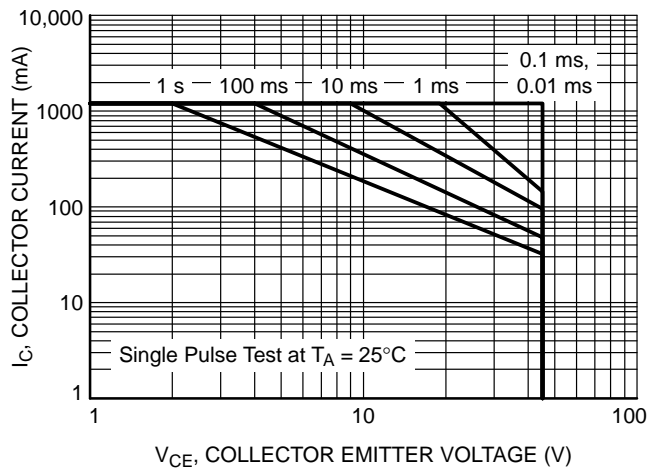
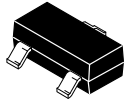


Figure 8. Safe Operating Area

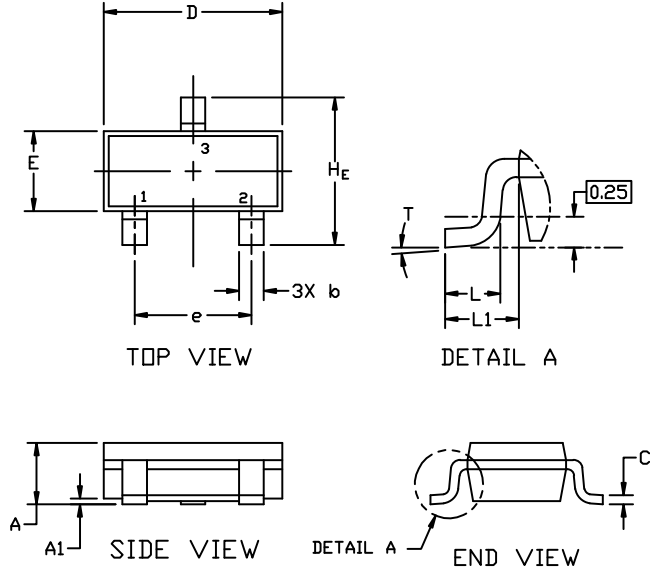
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

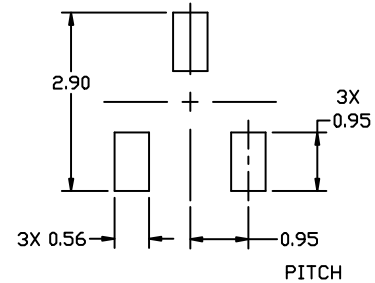
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H _E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

- | | | | | | |
|---|---|---|---|---|---|
| STYLE 1 THRU 5:
CANCELLED | STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE | | |
| STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE | STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE | STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE |
| STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE | STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE | STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE | STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE | STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE | STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE |
| STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT | STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE | STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE | STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION |
| STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE | STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE | | | | |

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